



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of

Cabral, Jr. et al.

Serial No.: 09/902,483

Group Art Unit: 2813

Filed: July 11, 2001

Examiner: Bowers, C.

#8  
1/23/02  
Harrison  
RECEIVED  
JAN 18 2002  
TECHNOLOGY CENTER 2800

For: SELF-ALIGNED SILICIDE (SALICIDE) PROCESS FOR LOW RESISTIVITY  
CONTACTS TO THIN FILM SILICIDE-ON-INSULATOR AND BULK MOSFETS  
AND FOR SHALLOW JUNCTIONS

Honorable Assistant Commissioner of Patents  
Washington, D.C. 20231

**RESPONSE TO FIRST OFFICE ACTION AND RESTRICTION  
REQUIREMENT**

Sir:

In response to the Office Action dated December 27, 2001, please consider the  
following:

**REMARKS**

In response to the Examiner's restriction requirement, Applicant hereby elects the  
invention of Group I (e.g., the semiconductor device as defined by claims 1-13), without  
traverse. Applicant reserves the opportunity to file a Divisional Application for the non-  
elected invention later.

Early, favorable prosecution on the merits is respectfully requested.

Should the Examiner find the application to be other than in condition for allowance,  
the Examiner is requested to contact the undersigned at the local telephone number listed  
below to discuss any other changes deemed necessary in a telephonic or personal interview.